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MEMC 02-0201 (3035.1)
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Milind Kulkarni
Serial No.: 10/705,813
Filed: November 10, 2003
Confirmation No.: 5409
For: CRYSTAL PULLER AND METHOD FOR
GROWING A MONOCRYSTALLINE INGOT

Art Unit: 1765

March 31, 2004

COMMISSIONER FOR PATENTS
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SIR:

INFORMATION DISCLOSURE STATEMENT

In accordance with 37 C.F.R. 1.97 and 1.98 and MPEP 609, and in compliance with the duty of disclosure set forth in 37 C.F.R. 1.56, applicant submits the attached PTO/SB/08A for consideration by the Patent and Trademark Office in the above-entitled application and to be made of record therein. In accordance with the Pre-OG notice of July 11, 2003 partially waiving the requirements of 37 C.F.R. 1.98(a)(2)(i), copies of the U.S. patent documents are not supplied. Applicant submits herewith copies of the foreign patent documents and literature references.

Respectfully submitted,

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MGM/clh

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PTO/SB/08A			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	10/705,813	
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			First Named Inventor	Milind Kulkarni	
			Group Art Unit	1765	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	4	Attorney Docket No.	MEMC 02-0201 (3035.1)

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
/RK/	1	4,597,949		Jasinski et al.	07-01-1986
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language translation is attached or place an "A" here if English language abstract is attached.

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		Office	Number ⁴	Kind Code ² (if known)			
/RK/	32	EP	0 890 662	A1	Shin-Etsu Handotai Company Ltd.	01-13-1999	

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/RK/	33	EP	0 903 427	A1	Shin-Etsu Handotai Co., Ltd.	03-24-1999	
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OTHER ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.					T ⁶
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Examiner Signature	/Robert Kunemund/	Date Considered	02/20/2009
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